

1SS294

PRV : 45 Volts
I_o : 100 mA

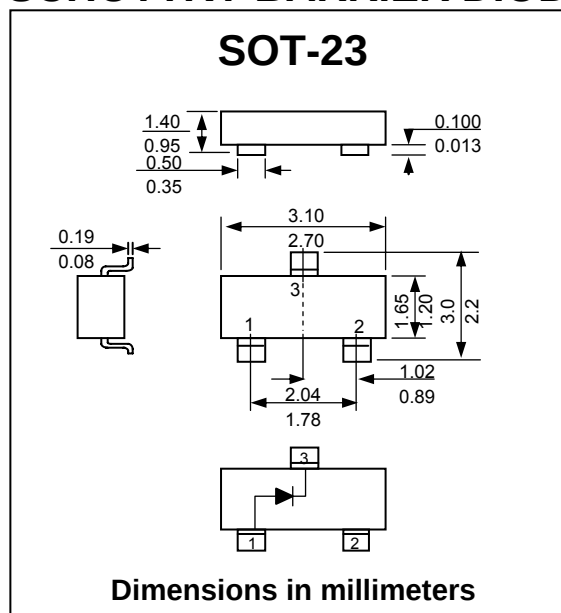
FEATURES :

- * Small surface mounting type
- * Low forward voltage
- * Low reverse current
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : SOT-23 plastic Case
- * Marking Code : " XM "

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE



MAXIMUM RATINGS AND THERMAL CHARACTERISTICS (Ta =25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	45	V
Reverse Voltage	V _R	40	V
Maximum Peak Forward Current	I _{FM}	300	mA
Average Forward Current	I _{F(AV)}	100	mA
Power Dissipation	P _D	150	mW
Junction Temperature	T _J	125	°C
Storage Temperature Range	T _{STG}	-55 to +125	°C

ELECTRICAL CHARACTERISTICS (Ta =25 °C)

Parameter	Test Condition	Symbol	Min.	Max.	Unit
Forward Voltage	I _F = 100 mA	V _F	-	0.6	V
Reverse Current	V _R = 40 V	I _R	-	5	μA
Total Capacitance	V _R = 0 V, f = 1 MHz	C _T	-	25	pF

RATINGS AND CHARACTERISTIC CURVES (1SS294)

FIG.1 - FORWARD CURRENT VS. FORWARD VOLTAGE

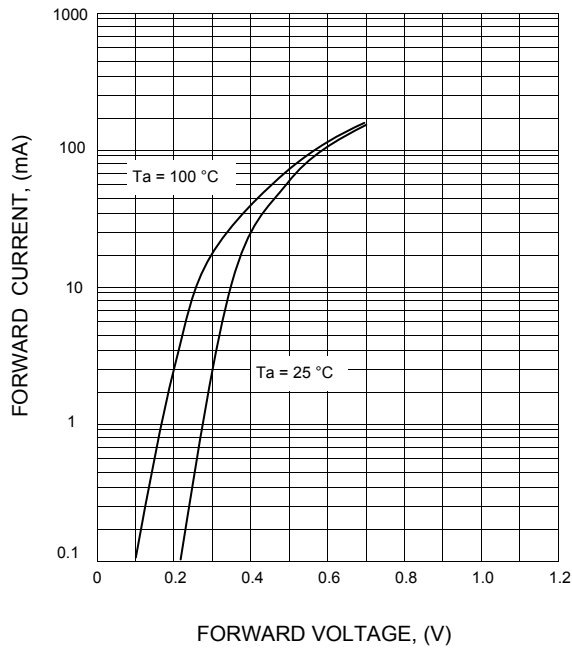


FIG.2 - REVERSE CURRENT VS. REVERSE VOLTAGE

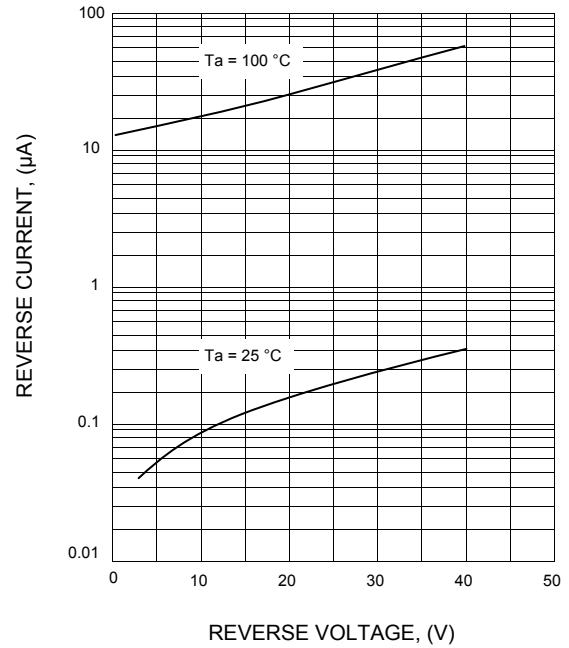


FIG.3 - TOTAL CAPACITANCE VS. REVERSE VOLTAGE

